2SA1797 TRANSISTOR (PNP)

FEATURES

- Low saturation voltage
- Excellent DC current gain characteristics
- Complements to 2SC4672

CLASSIFICATION of h_{FE}

Rank	P	Q	R
Range	82-180	120-270	180-390
Marking	AGP	AGQ	AGR

AGP AGQ AGR

Solid dot = Green molding compound device, the normal device

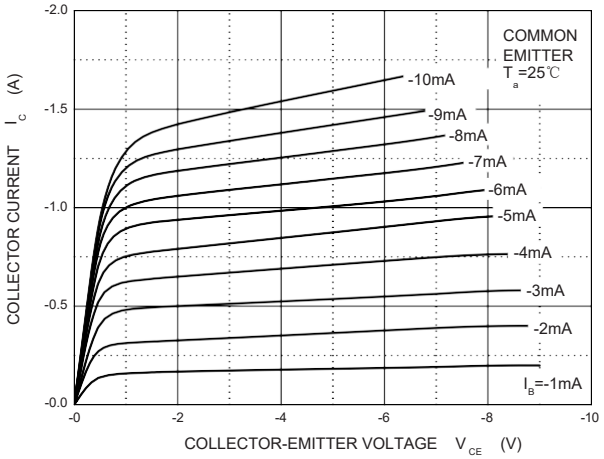
MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Continuous Collector Current	-2	A
I_{CM}	Peak Pluse Current	-3	A
P_C	Collector Power dissipation	500	mW
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~150	℃

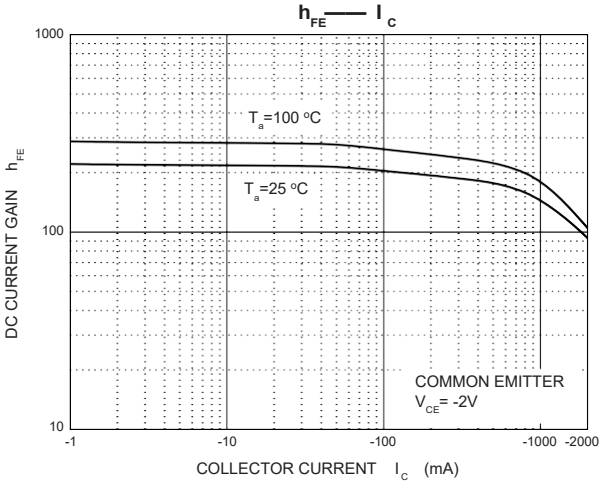
ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-50μA, I_E=0	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-50μA, I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}=-50V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-2V, I_C=-500mA	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-1A, I_B=-50mA			-0.35	V
Transition frequency	f_T	V_{CE}=-2V, I_C=-0.5A, f=100MHz		200		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		36		pF

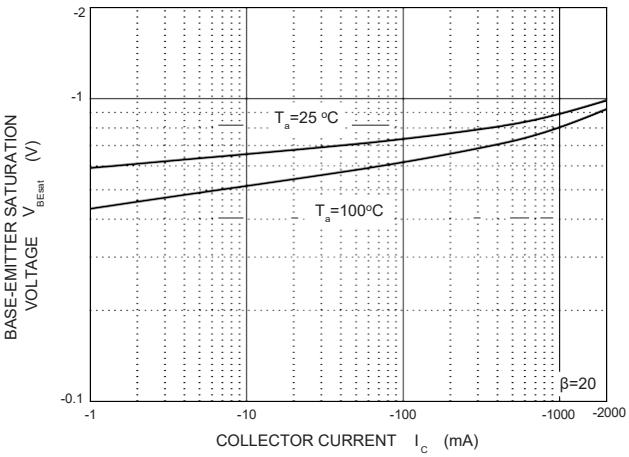
Static Characteristic



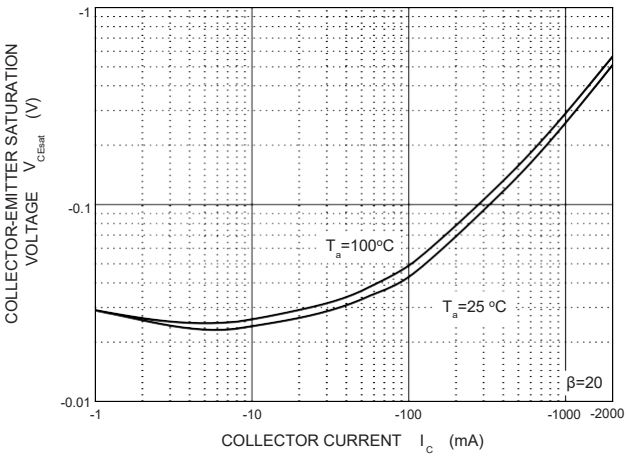
h_{FE} —— I_C



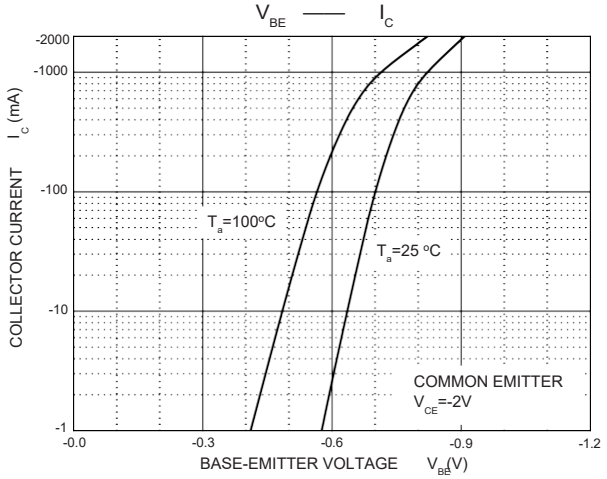
V_{BEsat} —— I_C



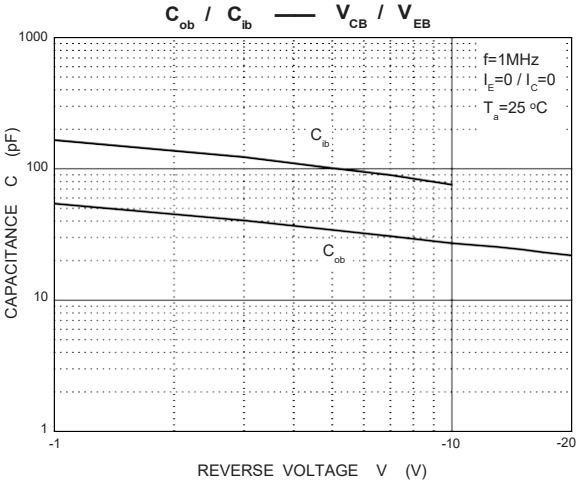
V_{CEsat} —— I_C



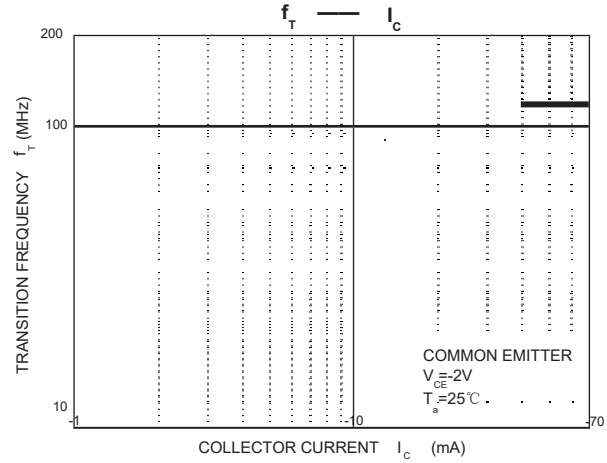
V_{BE} —— I_C



C_{ob} / C_{ib} —— V_{CB} / V_{EB}



f_T —— I_C



P_c —— T_a